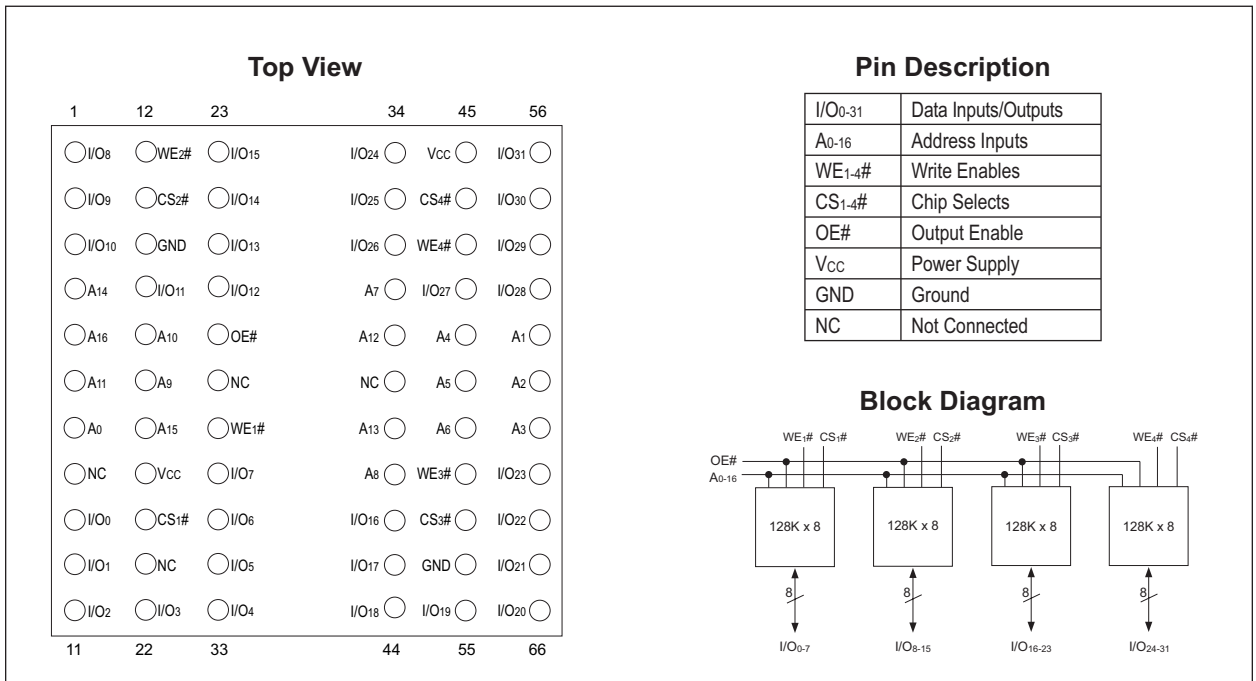


128Kx32 SRAM MODULE, SMD 5962-93187

FEATURES

- Access Times of 70, 85, 100, 120ns
- MIL-STD-883 Compliant Devices Available
- Packaging
 - 66-pin, PGA Type, 1.075 inch square, Hermetic Ceramic HIP (Package 400).
 - 68 lead, 40mm Low Profile CQFP, 3.56mm (0.140") (Package 502).
 - 68 lead, Hermetic CQFP (G2U), 22.4mm (0.880 inch) square, 4.57mm (0.140 inch) high, (Package 510)
- Organized as 128Kx32; User Configurable as 256Kx16 or 512Kx8
- Commercial, Industrial and Military Temperature Ranges
- 5 Volt Power Supply
- Low Power CMOS
- TTL Compatible Inputs and Outputs
- Built in Decoupling Caps and Multiple Ground Pins for Low Noise Operation
- Weight
 - WS128K32-XG2UX - 8 grams typical
 - WS128K32-XH1X - 13 grams typical
 - WS128K32-XG4TX - 20 grams typical
- Upgradeable to 512Kx32

FIGURE 1 – PIN CONFIGURATION FOR WS128K32N-XH1X



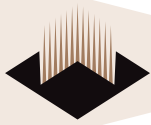


FIGURE 2 – PIN CONFIGURATION FOR WS128K32-XG4TX

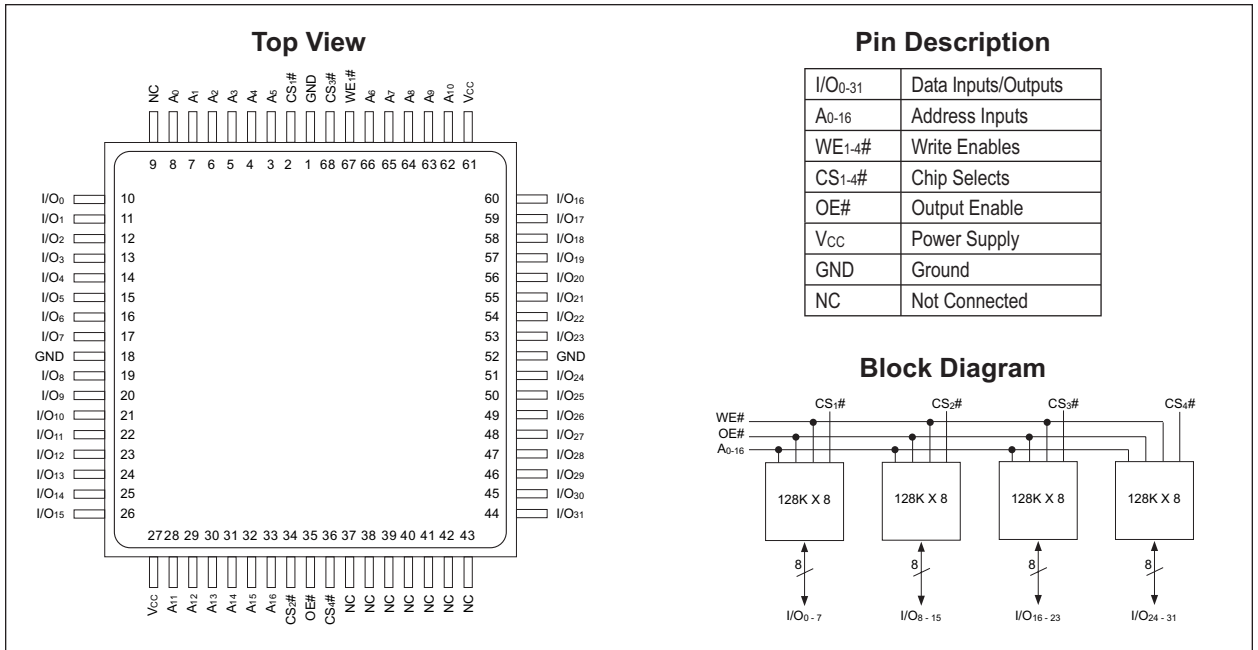
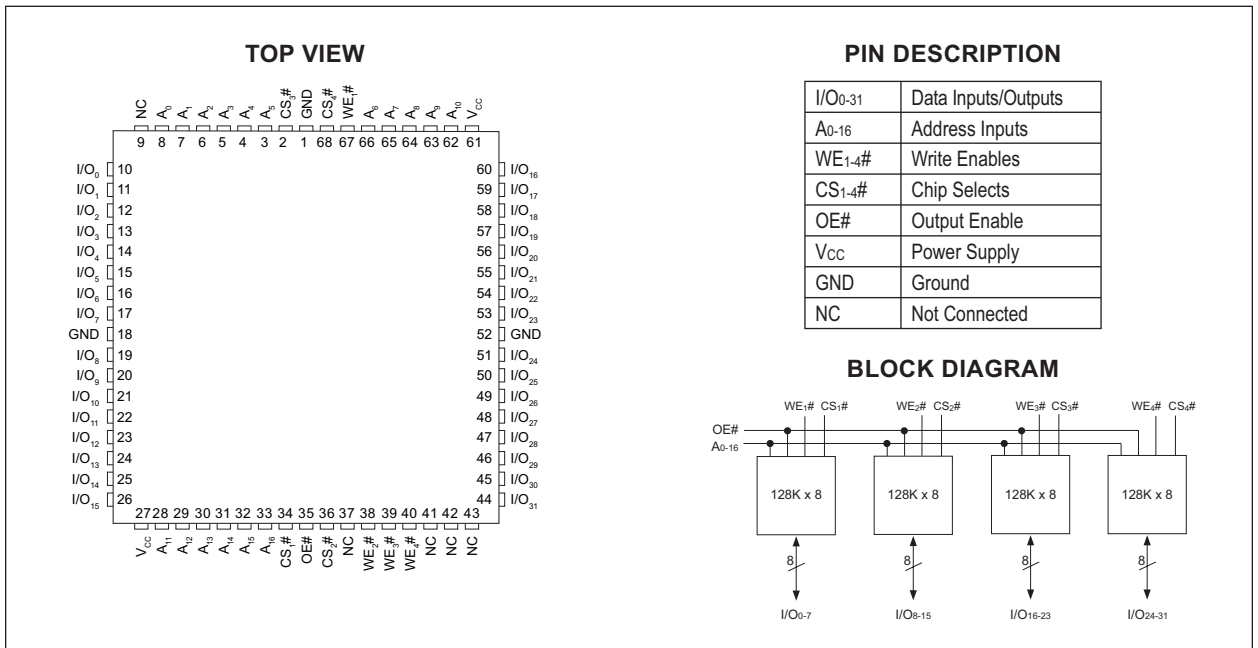


FIGURE 3 – PIN CONFIGURATION FOR WS128K32-XG2UX





ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Min	Max	Unit
Operating Temperature	T _A	-55	+125	°C
Storage Temperature	T _{STG}	-65	+150	°C
Signal Voltage Relative to GND	V _G	-0.5	V _{CC} +0.5	V
Junction Temperature	T _J		150	°C
Supply Voltage	V _{CC}	-0.5	7.0	V

TRUTH TABLE

CS	OE	WE	Mode	Data I/O	Power
H	X	X	Standby	High Z	Standby
L	L	H	Read	Data Out	Active
L	X	L	Write	Data In	Active
L	H	H	Out Disable	High Z	Active

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Min	Max	Unit
Supply Voltage	V _{CC}	4.5	5.5	V
Input High Voltage	V _{IH}	2.2	V _{CC} + 0.3	V
Input Low Voltage	V _{IL}	-0.5	+0.8	V

CAPACITANCE

T_A = +25°C

Parameter	Symbol	Conditions	Max	Unit
OE# capacitance	C _{OE}	V _{IN} = 0V, f = 1.0 MHz	50	pF
WE1-4# capacitance HIP (PGA) CQFP G4T CQFP G2U	C _{WE}	V _{IN} = 0V, f = 1.0 MHz	20 50 15	pF
CS1-4# capacitance	C _{CS}	V _{IN} = 0V, f = 1.0 MHz	20	pF
Data# I/O capacitance	C _{I/O}	V _{I/O} = 0V, f = 1.0 MHz	20	pF
Address input capacitance	C _{AD}	V _{IN} = 0V, f = 1.0 MHz	50	pF

This parameter is guaranteed by design but not tested.

DC CHARACTERISTICS

V_{CC} = 5.0V, V_{SS} = 0V, -55°C ≤ T_A ≤ +125°C

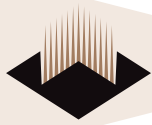
Parameter	Sym	Conditions	-70		-85		-100		-120		Units
			Min	Max	Min	Max	Min	Max	Min	Max	
Input Leakage Current	I _{LI}	V _{CC} = 5.5, V _{IN} = GND to V _{CC}		10		10		10		10	µA
Output Leakage Current	I _{LO}	CS# = V _{IH} , OE# = V _{IH} , V _{OUT} = GND to V _{CC}		10		10		10		10	µA
Operating Supply Current	I _{CC}	CS# = V _{IL} , OE# = V _{IH} , f = 5MHz, V _{CC} = 5.5		120		120		120		120	mA
Standby Current	I _{SB}	CS# = V _{IH} , OE# = V _{IH} , f = 5MHz, V _{CC} = 5.5		20		20		20		20	mA
Output Low Voltage	V _{OL}	I _{OL} = 2.1mA, V _{CC} = 4.5		0.4		0.4		0.4		0.4	V
Output High Voltage	V _{OH}	I _{OH} = -1.0mA, V _{CC} = 4.5	2.4		2.4		2.4		2.4		V

NOTE: DC test conditions: V_{IH} = V_{CC} - 0.3V, V_{IL} = 0.3V

DATA RETENTION CHARACTERISTICS

-55°C ≤ T_A ≤ +125°C

Parameter	Sym	Conditions	-70		-85		-100		-120		Units
			Min	Max	Min	Max	Min	Max	Min	Max	
Data Retention Supply Voltage	V _{DR}	CS ≥ V _{CC} - 0.2V	2.0	5.5	2.0	5.5	2.0	5.5	2.0	5.5	V
Data Retention Current	I _{CCDR1}	V _{CC} = 3V		4		4		4		4	mA



AC CHARACTERISTICS

V_{CC} = 5.0V, GND = 0V, -55°C ≤ T_A ≤ +125°C

Parameter Read Cycle	Symbol	-70		-85		-100		-120		Units
		Min	Max	Min	Max	Min	Max	Min	Max	
Read Cycle Time	t _{RC}	70		85		100		120		ns
Address Access Time	t _{AA}		70		85		100		120	ns
Output Hold from Address Change	t _{OH}	3		3		3		3		ns
Chip Select Access Time	t _{ACS}		70		85		100		120	ns
Output Enable to Output Valid	t _{OE}		35		45		50		60	ns
Chip Select to Output in Low Z	t _{CLZ} ¹	3		3		3		3		ns
Output Enable to Output in Low Z	t _{OLZ} ¹	0		0		0		0		ns
Chip Disable to Output in High Z	t _{CHZ} ¹		25		25		35		35	ns
Output Disable to Output in High Z	t _{OHZ} ¹		25		25		35		35	ns

AC CHARACTERISTICS

V_{CC} = 5.0V, GND = 0V, -55°C ≤ T_A ≤ +125°C

Parameter Write Cycle	Symbol	-70		-85		-100		-120		Units
		Min	Max	Min	Max	Min	Max	Min	Max	
Write Cycle Time	t _{WC}	70		85		100		120		ns
Chip Select to End of Write	t _{CW}	60		75		80		100		ns
Address Valid to End of Write	t _{AW}	60		75		80		100		ns
Data Valid to End of Write	t _{DW}	30		35		40		50		ns
Write Pulse Width	t _{WP}	50		55		70		80		ns
Address Setup Time	t _{AS}	5		5		5		5		ns
Address Hold Time	t _{AH}	5		5		5		5		ns
Output Active from End of Write	t _{OW} ¹	5		5		5		5		ns
Write Enable to Output in High Z	t _{WHZ} ¹		25		25		35		35	ns
Data Hold Time	t _{DH}	0		0		0		0		ns

1. This parameter is guaranteed by design but not tested.

FIGURE. 4 – AC TEST CIRCUIT

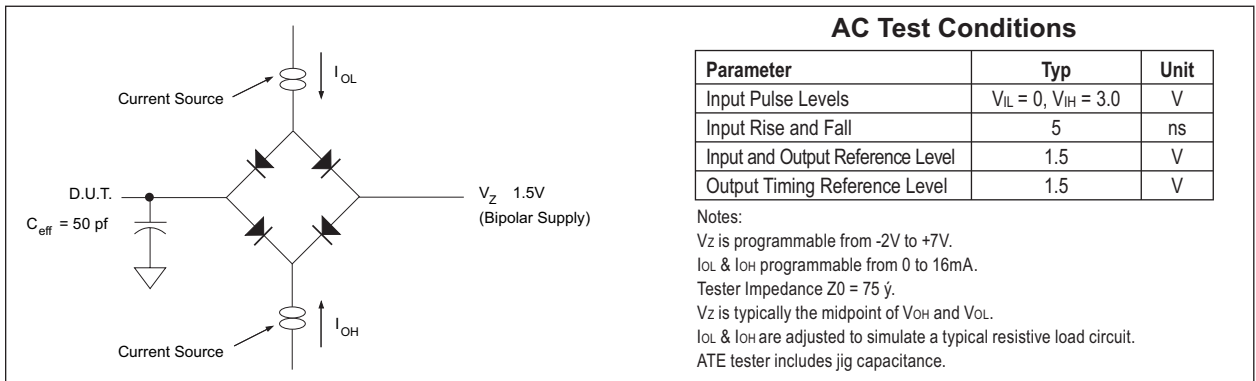




FIGURE 5 – TIMING WAVEFORM - READ CYCLE

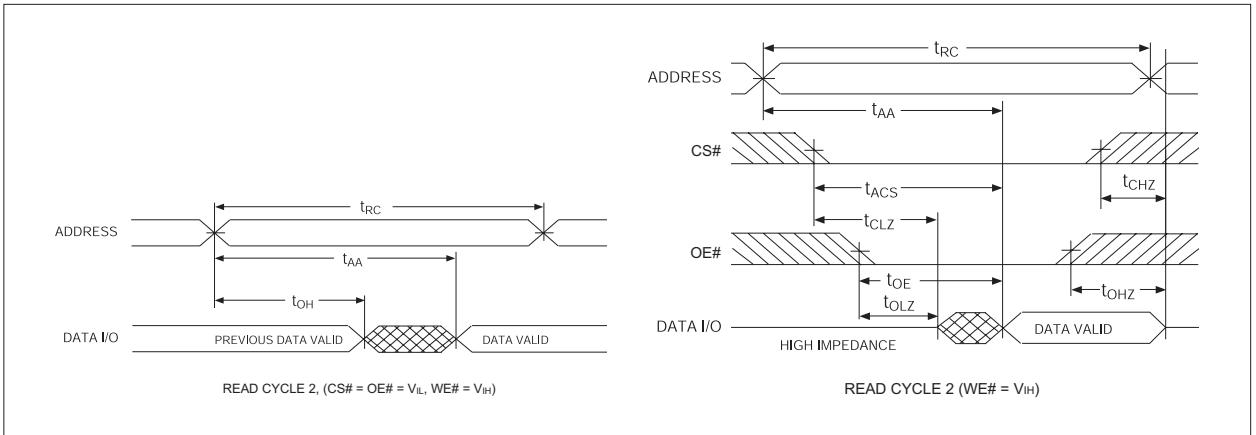


FIGURE 6 – WRITE CYCLE - WE# CONTROLLED

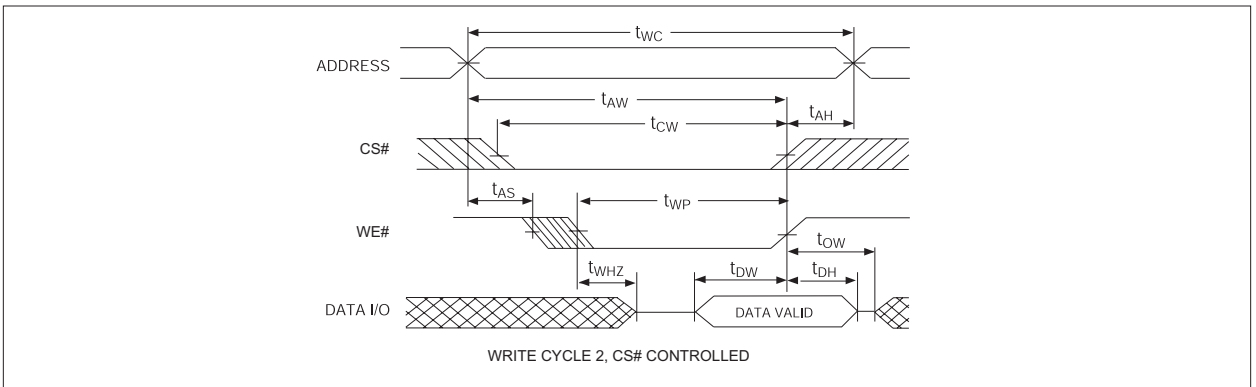
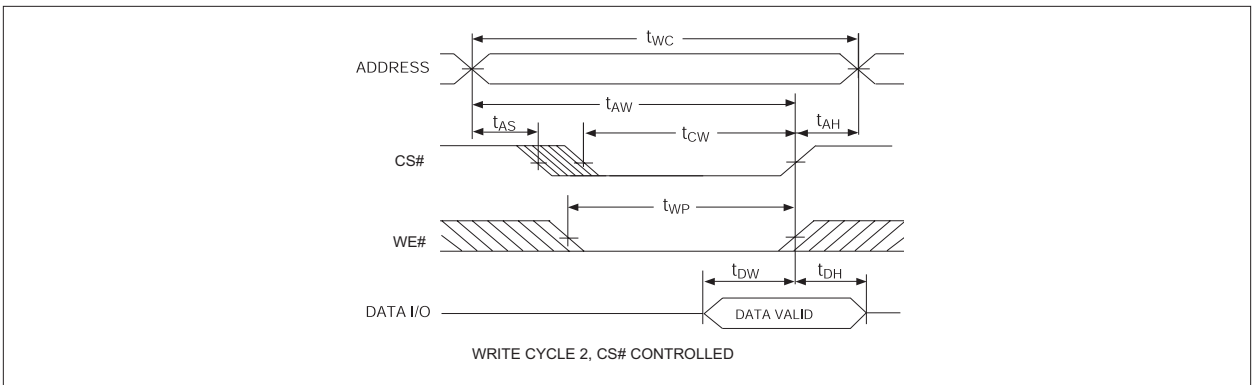
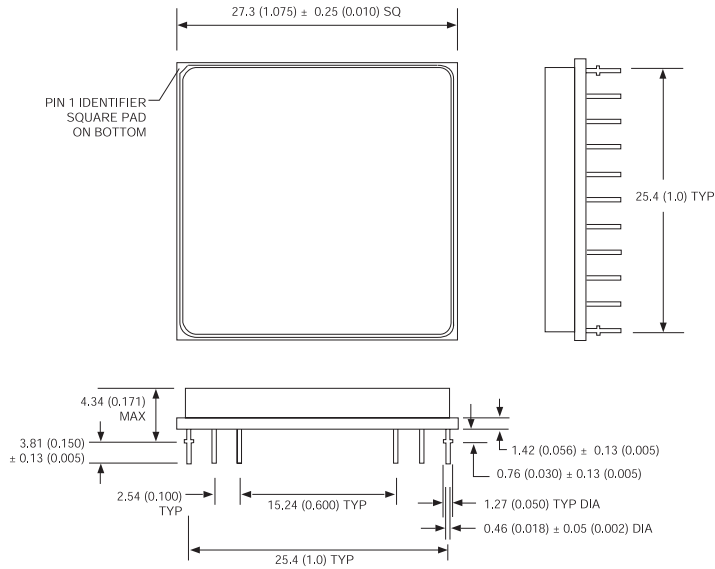


FIGURE 7 – WRITE CYCLE - CS# CONTROLLED



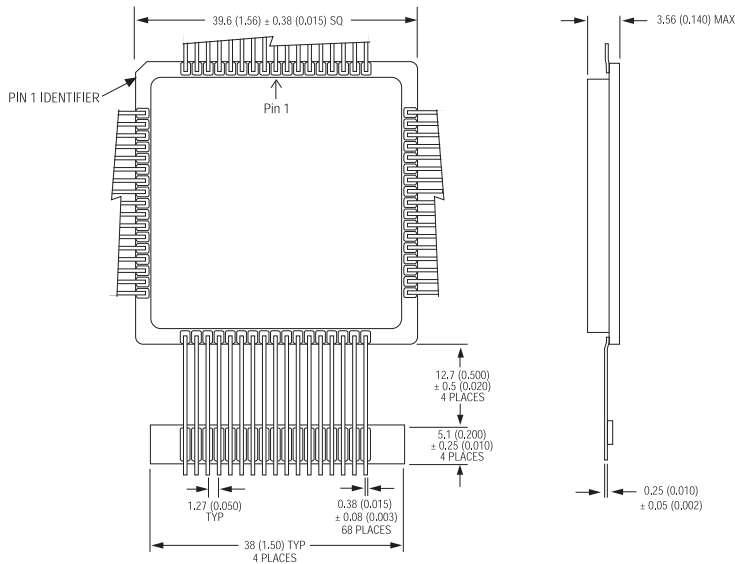


PACKAGE 400: 66 PIN, PGA TYPE, CERAMIC HEX-IN-LINE PACKAGE, HIP (H1)



ALL LINEAR DIMENSIONS ARE MILLIMETERS AND PARENTHETICALLY IN INCHES

PACKAGE 502: 68 LEAD, CERAMIC QUAD FLAT PACK, LOW PROFILE CQFP (G4T)¹



ALL LINEAR DIMENSIONS ARE MILLIMETERS AND PARENTHETICALLY IN INCHES



ORDERING INFORMATION

W S 128K 32 X - XXX X X X

LEAD FINISH:

- Blank = Gold plated leads
- A = Solder dip leads

DEVICE GRADE:

- Q = MIL-STD-883 Compliant
- M = Military Screened -55°C to +125°C
- I = Industrial -40°C to +85°C
- C = Commercial 0°C to +70°C

PACKAGE TYPE:

- H1 = 1.075" sq. Ceramic Hex-In-line Package, HIP (Package 400)
- G2U = 22.4mm Ceramic Quad Flat Pack, Low Profile CQFP (Package 510)
- G4T = 40 mm Low Profile CQFP (Package 502)

ACCESS TIME (ns)

IMPROVEMENT MARK:

- N = No Connect at pin 8, 21, 28 and 39 in HIP for Upgrades

ORGANIZATION, 128Kx32

- User configurable as 256Kx16 or 512Kx8

SRAM

WHITE ELECTRONIC DESIGNS CORPORATION



DEVICE TYPE	SPEED	PACKAGE	SMD NO.
128K x 32 SRAM Module	120ns	66 pin HIP (H1)	5962-93187 01H5X
128K x 32 SRAM Module	100ns	66 pin HIP (H1)	5962-93187 02H5X
128K x 32 SRAM Module	85ns	66 pin HIP (H1)	5962-93187 03H5X
128K x 32 SRAM Module	70ns	66 pin HIP (H1)	5962-93187 04H5X
128K x 32 SRAM Module	120ns	68 lead CQFP/J (G2U)	5962-95595 01HNX
128K x 32 SRAM Module	100ns	68 lead CQFP/J (G2U)	5962-95595 02HNX
128K x 32 SRAM Module	85ns	68 lead CQFP/J (G2U)	5962-95595 03HNX
128K x 32 SRAM Module	70ns	68 lead CQFP/J (G2U)	5962-95595 04HNX
128K x 32 SRAM Module	120ns	68 lead CQFP Low Profile (G4T)	5962-95595 01HYX
128K x 32 SRAM Module	100ns	68 lead CQFP Low Profile (G4T)	5962-95595 02HYX
128K x 32 SRAM Module	85ns	68 lead CQFP Low Profile (G4T)	5962-95595 03HYX
128K x 32 SRAM Module	70ns	68 lead CQFP Low Profile (G4T)	5962-95595 04HYX